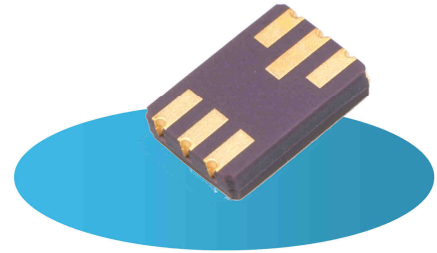


2N2222ADCSM

- Dual High Speed Saturated Switching Transistor
- Hermetic Ceramic Surface Mount Package
- Screening Options Available

**ABSOLUTE MAXIMUM RATINGS** ($T_A = 25^\circ\text{C}$ unless otherwise stated), Per Device

V_{CBO}	Collector – Base Voltage	75V
V_{CEO}	Collector – Emitter Voltage	40V
V_{EBO}	Emitter – Base Voltage	6V
I_C	Continuous Collector Current	0.8A
P_D	Total Power Dissipation at $T_A = 25^\circ\text{C}$ Derate Above 25°C	500mW 2.86mW/ $^\circ\text{C}$
T_J	Junction Temperature Range	-65 to $+200^\circ\text{C}$
T_{stg}	Storage Temperature Range	-65 to $+200^\circ\text{C}$

THERMAL PROPERTIES

Symbols	Parameters	Max.	Units
$R_{\theta JA}^{(1)}$	Thermal Resistance, Junction To Ambient	350	$^\circ\text{C}/\text{W}$
$R_{\theta JSP}^{(2)}$	Thermal Resistance, Junction To Solder Pads	110	$^\circ\text{C}/\text{W}$

Notes

- (1) For non-thermal conductive PCB or unknown PCB surface mount conditions in free air.
 (2) Infinite sink mount to PCB

Semelab Limited reserves the right to change test conditions, parameter limits and package dimensions without notice. Information furnished by Semelab is believed to be both accurate and reliable at the time of going to press. However Semelab assumes no responsibility for any errors or omissions discovered in its use. Semelab encourages customers to verify that datasheets are current before placing orders.

SEMELAB 

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DUAL SILICON SWITCHING NPN TRANSISTORS

2N2222ADCSM



ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise stated), Per Device

Symbols	Parameters	Test Conditions	Min.	Typ.	Max.	Units
$V_{(BR)CEO}^{(3)}$	Collector-Emitter Breakdown Voltage	$I_C = 10\text{mA}$	40			V
$V_{(BR)CBO}$	Collector-Base Breakdown Voltage	$I_C = 10\mu\text{A}$	75			
$V_{(BR)EBO}$	Emitter-Base Breakdown Voltage	$I_E = 10\mu\text{A}$	6			
I_{CEX}	Collector-Emitter Cut-Off Current	$V_{EB} = 3\text{V}$ $V_{CE} = 60\text{V}$			10	nA
I_{CBO}	Collector-Base Cut-Off Current	$I_E = 0$ $V_{CB} = 60\text{V}$ $T_A = 150^\circ\text{C}$			10	
I_{EBO}	Emitter Cut-Off Current	$I_C = 0$ $V_{EB} = 3\text{V}$			10	nA
$V_{CE(Sat)}^{(3)}$	Collector-Emitter Saturation Voltage	$I_C = 150\text{mA}$ $I_B = 15\text{mA}$			0.3	V
		$I_C = 500\text{mA}$ $I_B = 50\text{mA}$			1.0	
$V_{BE(Sat)}^{(3)}$	Base-Emitter Saturation Voltage	$I_C = 150\text{mA}$ $I_B = 15\text{mA}$	0.6		1.2	
		$I_C = 500\text{mA}$ $I_B = 50\text{mA}$			2.0	
$h_{FE}^{(3)}$	DC Current Gain	$I_C = 0.1\text{mA}$ $V_{CE} = 10\text{V}$	35			-
		$I_C = 1.0\text{mA}$ $V_{CE} = 10\text{V}$	50			
		$I_C = 10\text{mA}$ $V_{CE} = 10\text{V}$ $T_A = -55^\circ\text{C}$	75			
		$I_C = 150\text{mA}$ $V_{CE} = 10\text{V}$	100		300	
		$I_C = 150\text{mA}$ $V_{CE} = 1.0\text{V}$	50			
		$I_C = 500\text{mA}$ $V_{CE} = 10\text{V}$	40			

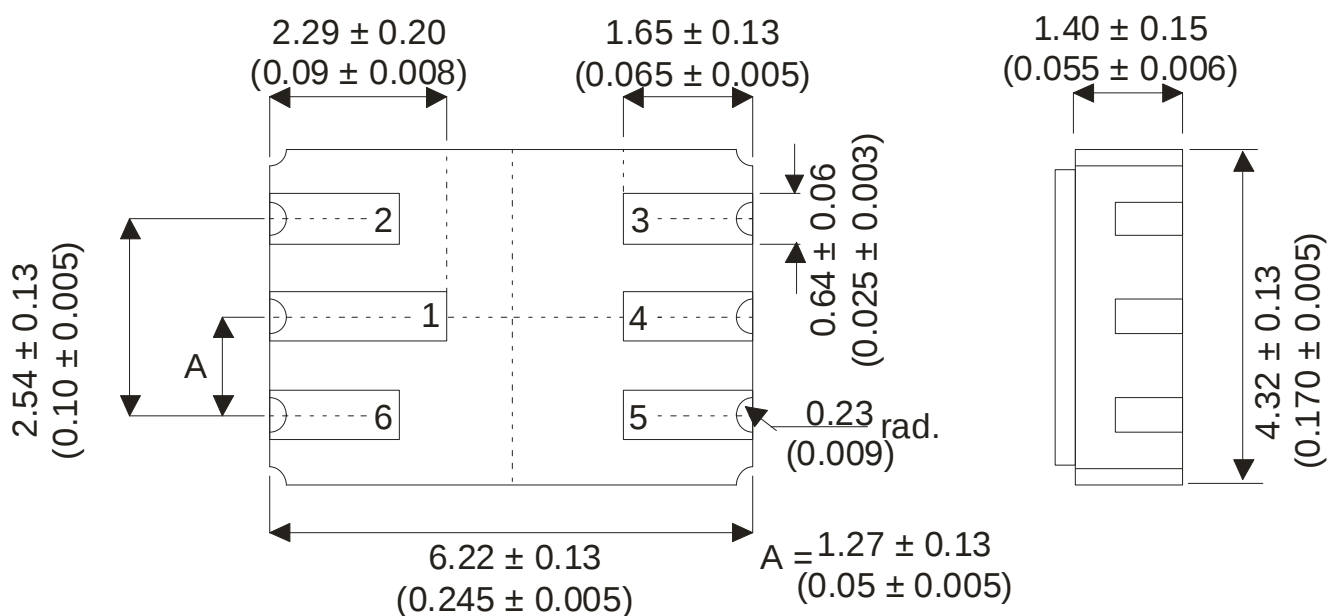
DYNAMIC CHARACTERISTICS

C_{obo}	Output Capacitance	$V_{CB} = 10\text{V}$ $I_E = 0$ $f = 1.0\text{MHz}$			8	pF
C_{ibo}	Input Capacitance	$V_{EB} = 0.5\text{V}$ $I_C = 0$ $f = 1.0\text{MHz}$			30	
f_t	Transition Frequency	$I_C = 20\text{mA}$ $V_{CE} = 20\text{V}$ $f = 100\text{MHz}$	300			MHz
h_{fe}	Small Signal Current Gain	$I_C = 1.0\text{mA}$ $V_{CE} = 10\text{V}$ $f = 1.0\text{kHz}$	50		300	-
		$I_C = 10\text{mA}$ $V_{CE} = 10\text{V}$ $f = 1.0\text{kHz}$	75		375	
t_d	Delay Time	$V_{CC} = 30\text{V}$ $V_{BE} = 0.5\text{V}$			10	ns
t_r	Rise Time	$I_C = 150\text{mA}$ $I_{B1} = 15\text{mA}$			25	
t_s	Storage Time	$V_{CC} = 30\text{V}$ $V_{BE} = 0.5\text{V}$			225	
t_f	Fall Time	$I_C = 150\text{mA}$ $I_{B1} = I_{B2} = 15\text{mA}$			60	

Note

(3) Pulse Width $\leq 380\mu\text{s}$, $\delta \leq 2\%$

Dimensions in mm (inches)



Pad 1 – Collector 1 Pad 4 – Collector 2
Pad 2 – Base 1 Pad 5 – Emitter 2
Pad 3 – Base 2 Pad 6 – Emitter 1